



STS4DNF60L

N-channel 60 V, 0.045 Ω , 4 A, SO-8
STripFET™ Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)}	I _D
STS4DNF60L	60V	<0.055 Ω	4A

- Standard outline for easy automated surface mount assembly
- Low threshold drive

Application

- Switching applications

Description

This Power MOSFET is the latest development of STMicroelectronics unique “single feature size” strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

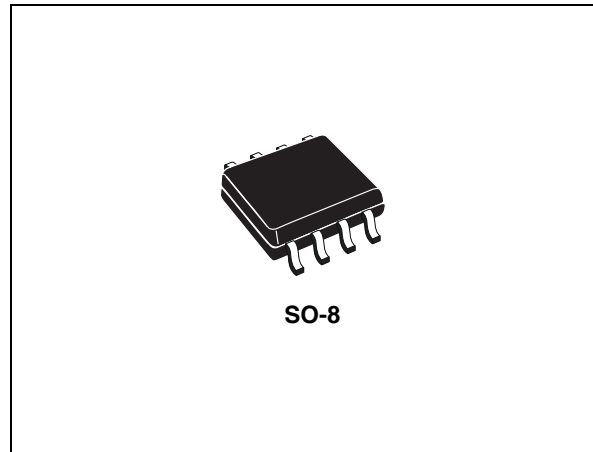


Figure 1. Internal schematic diagram

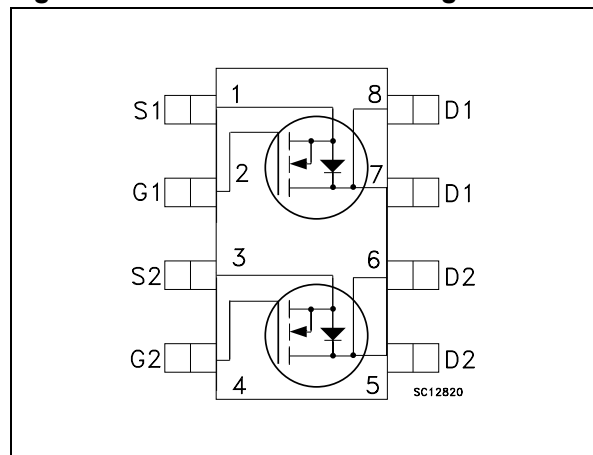


Table 1. Device summary

Order code	Marking	Package	Packaging
STS4DNF60L	4DF60L	SO-8	Tape & reel

Contents

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	60	V
V_{GS}	Gate- source voltage	± 15	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	4	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	2.5	A
$I_{DM}^{(1)}$	Drain current (pulsed)	16	A
$P_{TOT}^{(2)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	2	W
$E_{AS}^{(3)}$	Single pulse avalanche energy	80	mJ
T_j T_{stg}	Operating junction temperature Storage temperature	- 55 to 150	$^\circ\text{C}$

1. Pulse width limited by safe operating area
2. $P_{TOT}=1.6\text{ W}$ for single operation
3. Starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = 4\text{ A}$, $V_{DD} = 30\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-pcb}$	Thermal resistance junction-pcb D.O. ⁽¹⁾	62.5	$^\circ\text{C/W}$

1. When mounted on inch² FR-4 board, 2 Oz Cu, $t \leq 10\text{sec}$, dual operation

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0$	60			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$, $T_C = 125\text{ °C}$			1 10	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 15\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	1	1.7	2.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 2\text{ A}$ $V_{GS} = 4.5\text{ V}$, $I_D = 2\text{ A}$		0.045 0.050	0.055 0.065	Ω Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs}	Forward transconductance	$V_{DS} = 25\text{ V}$, $I_D = 2\text{ A}$	-	25	-	S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	1030 140 40	-	pF pF pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 48\text{ V}$, $I_D = 4\text{ A}$, $V_{GS} = 4.5\text{ V}$ (see Figure 13)	-	15 4 4	-	nC nC nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	$V_{DD} = 30\text{ V}$, $I_D = 2.2\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 12)	-	15 28	-	ns ns
$t_{d(off)}$ t_f	Turn-off delay time Fall time		-	45 10	-	ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		4	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		16	A		
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 4\text{ A}$, $V_{GS} = 0$	-		1.2	V
t_{rr}	Reverse recovery time	$I_{SD} = 4\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 20\text{ V}$ (see Figure 17)	-	85		ns
Q_{rr}	Reverse recovery charge		85	nC		
I_{RRM}	Reverse recovery current		2	A		

1. Pulse width limited by safe operating area

2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

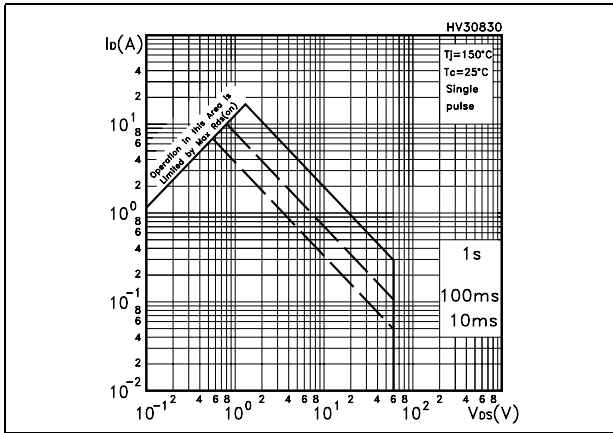


Figure 3. Thermal impedance

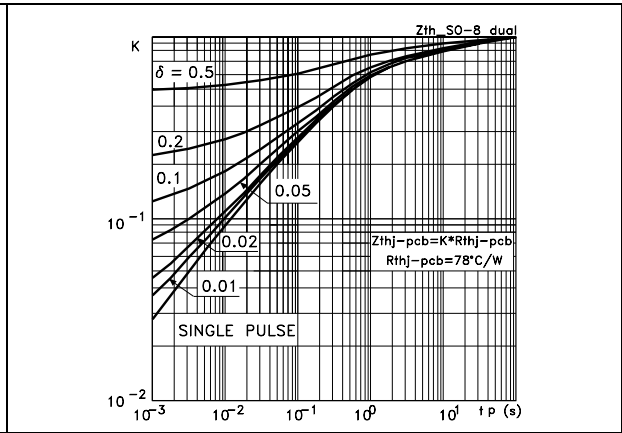


Figure 4. Output characteristics

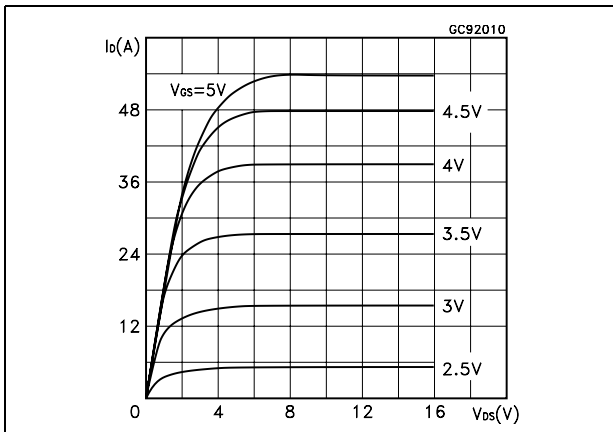


Figure 5. Transfer characteristics

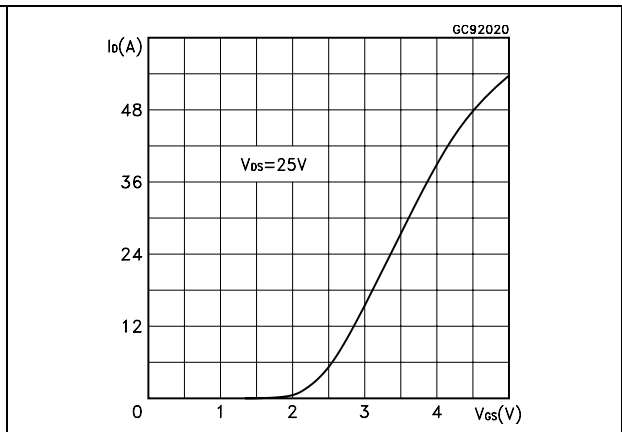


Figure 6. Source-drain diode forward characteristics

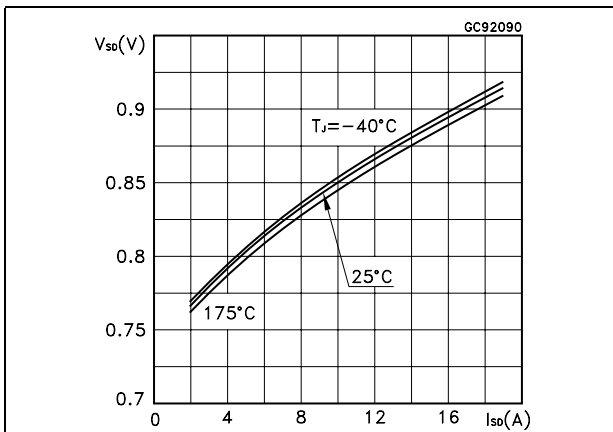


Figure 7. Static drain-source on resistance

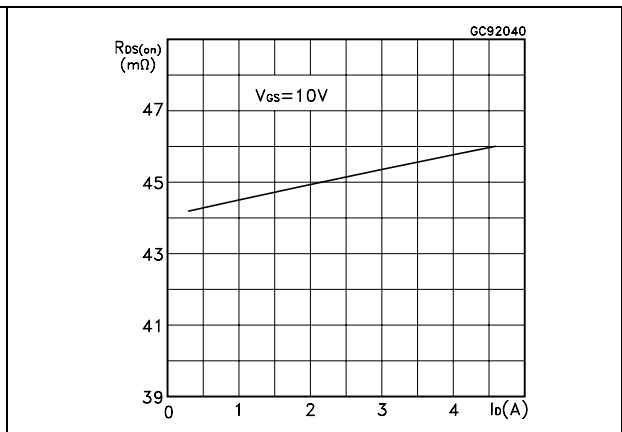


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

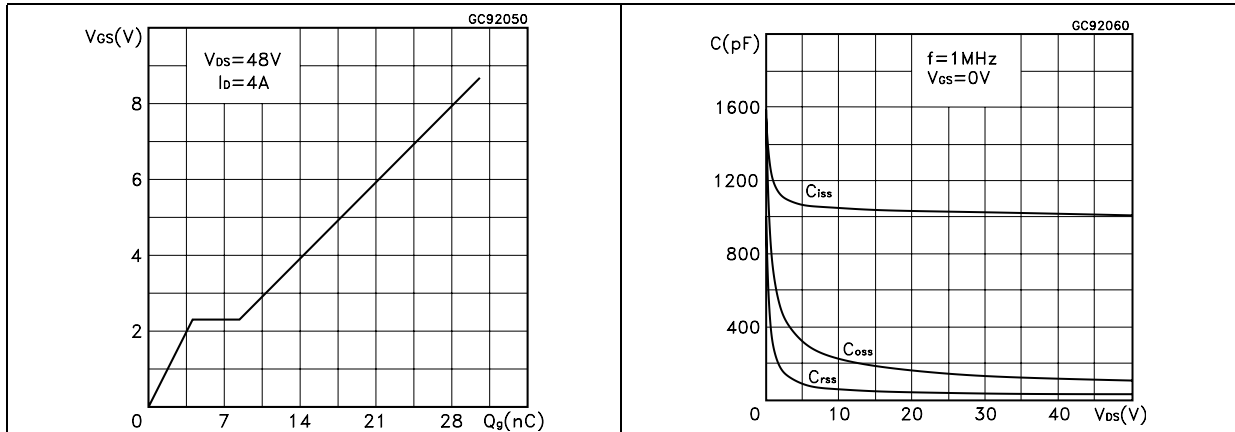
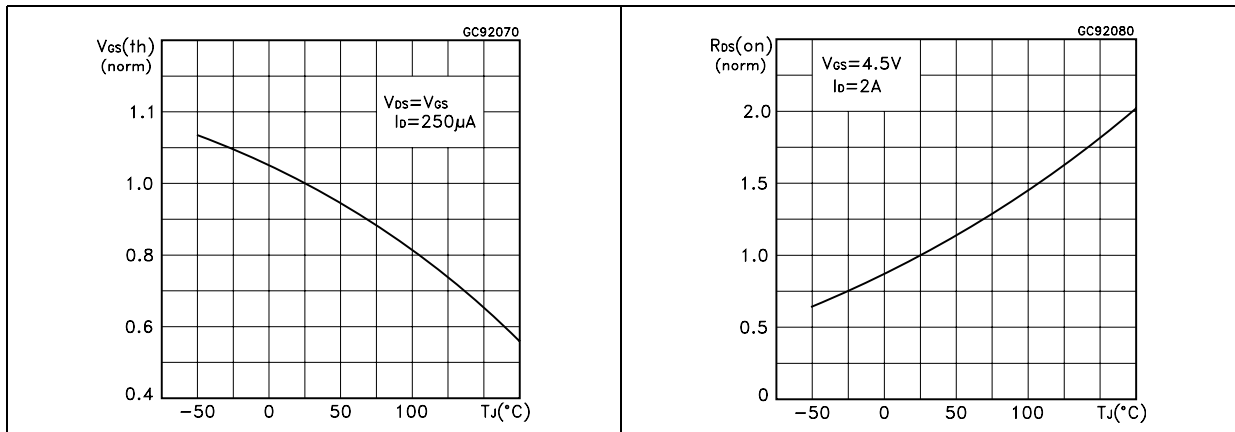
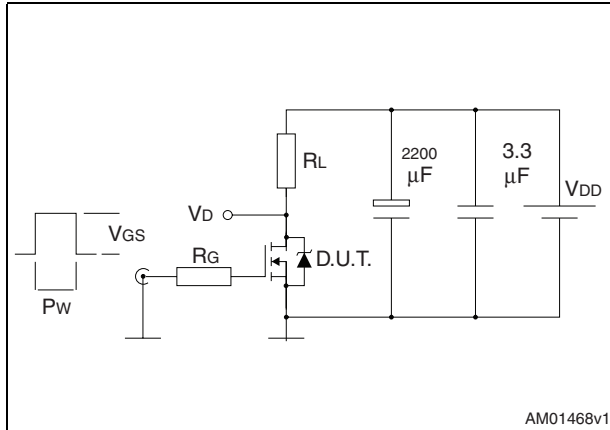


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature



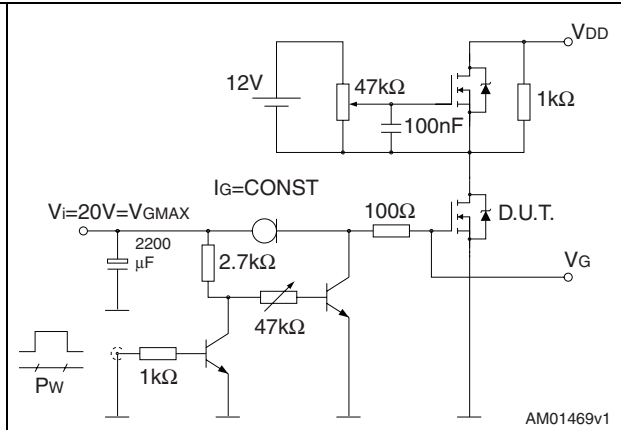
3 Test circuits

Figure 12. Switching times test circuit for resistive load



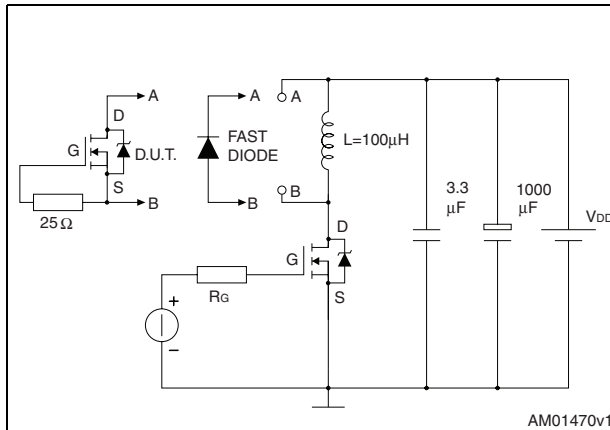
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Figure 13. Gate charge test circuit



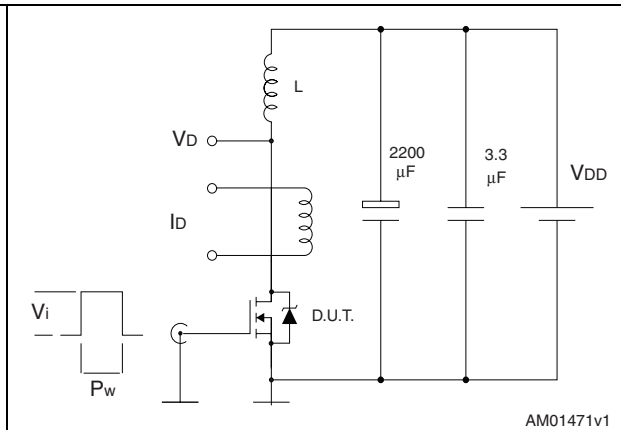
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Figure 14. Test circuit for inductive load switching and diode recovery times



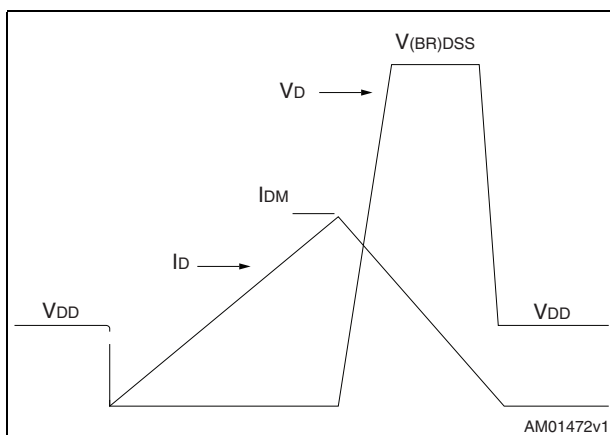
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Figure 15. Unclamped Inductive load test circuit



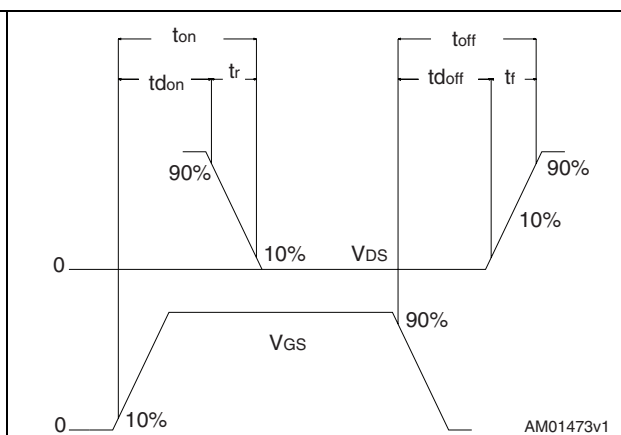
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Figure 16. Unclamped inductive waveform



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Figure 17. Switching time waveform



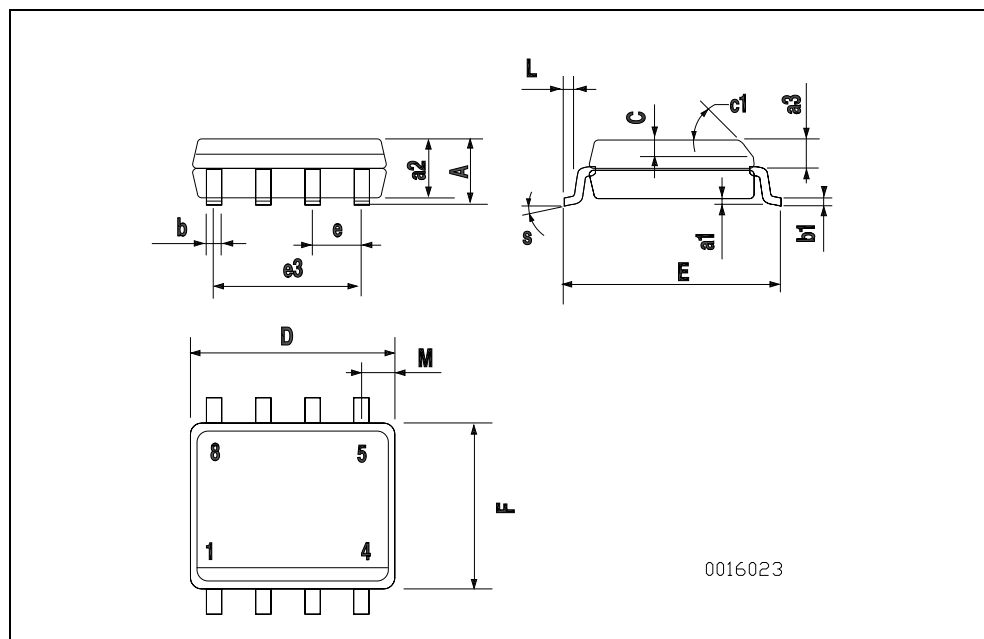
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4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

SO-8 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					



5 Revision history

Table 8. Document revision history

Date	Revision	Changes
30-May-2005	5	Initial electronic version
29-Mar-2006	6	Modified Figure 2 and Figure 3
16-May-2006	7	Modified internal schematic diagram
29-Aug-2007	8	Marking has been updated
30-Mar-2010	9	Inserted E_{AS} value in Table 2: Absolute maximum ratings

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